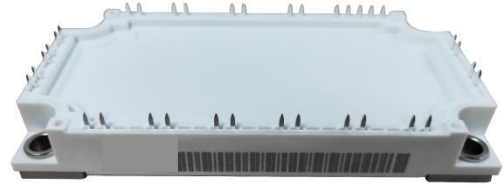


Electrical Features

- Trench/ Fieldstop IGBT
- V_{CEsat} with positive Temperature Coefficient
- Low V_{CEsat}

Typical Applications

- Auxiliary inverters
- Motor drives
- Servo drives



Mechanical Features

- High power density
- Integrated NTC temperature sensor
- Copper base plate
- Solder contact technology
- Standard housing

IGBT , Inverter

Maximum Rated Values							
Symbol	Item	Conditions	Rating			Unit	
IGBT							
V_{CES}	Collector-emitter voltage	$T_{vj}=25^{\circ}C$	1200			V	
V_{GES}	Gate-emitter voltage	-	± 20			V	
I_C	Collector current,DC	$T_C=100^{\circ}C, T_{vj}=175^{\circ}C$	75			A	
I_{CRM}	Repetitive peak collector current	$t_p=1ms$	150			A	
P_{tot}	Total power dissipation	$T_C=25^{\circ}C, T_{vj}=175^{\circ}C$	428			W	
Characteristics Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=1200V, V_{GE}=0V, T_{vj}=25^{\circ}C$	-	-	1	mA	
I_{GES}	Gate leakage current	$V_{CE}=0V, V_{GE}=20V, T_{vj}=25^{\circ}C$	-	-	500	nA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=2.4mA, V_{CE}=V_{GE}, T_{vj}=25^{\circ}C$	5.2	5.60	6.2	V	
V_{CEsat}	Collector-emitter saturation voltage	$I_C=75A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	1.92	-	V
			$T_{vj}=125^{\circ}C$	-	-	-	
			$T_{vj}=150^{\circ}C$	-	-	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$	-	5.30	-	nF	
C_{oes}	Output capacitance		-	0.35	-		
C_{res}	Reverse transfer capacitance		-	0.18	-		
Q_G	Gate charge	$V_{CC}=600V, I_C=75A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$	-	477	-	nC	
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	2.4	-	Ω	

$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $I_C=75A$ $V_{GE}=\pm 15V$ $R_{G(on)}=10\Omega$ $R_{G(off)}=10\Omega$	$T_{vj}=25^\circ C$	-	78.5	-	ns
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_r	Rise time		$T_{vj}=25^\circ C$	-	65.1	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^\circ C$	-	346.8	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_f	Fall time		$T_{vj}=25^\circ C$	-	201.8	-	
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^\circ C$	-	9.06	-	mJ	
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^\circ C$	-	4.21	-		
		$T_{vj}=125^\circ C$	-	-	-		
		$T_{vj}=150^\circ C$	-	-	-		
SC data	Short-circuit current	$V_{CC}=600V, V_{GE}\leq 15V, T_{vj}=125^\circ C$ $V_{CES}\leq 1200V, t_p\leq 10\mu s$	-	395	-	A	
R_{thJC}	Thermal resistance, junction to case	Per IGBT	-	-	0.35	K/W	
R_{thCH}	Thermal resistance, case to heatsink	Per IGBT $\lambda_{grease}=1W/(m\cdot K)$	-	0.125	-	K/W	
T_{vjop}	Temperature under switching conditions		-40		150	$^\circ C$	

Diode , Inverter
Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^\circ C$	1200	V
I_F	Forward current, DC		75	A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	150	A
I^2t	I^2t -value	$V_R=0V, t_p=10ms, T_{vj}=125^\circ C$	1200	A^2s

Characteristic Values

V_F	Continuous forward voltage	$I_F=75A$ $V_{GE}=0V$	$T_{vj}=25^\circ C$	-	2.01	-	V
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
I_{RM}	Peak reverse recovery current		$T_{vj}=25^\circ C$	-	61.5	-	A
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
t_{rr}	Reverse recovery time	$V_R=600V$ $I_F=75A$ $V_{GE}=-15V$	$T_{vj}=25^\circ C$	-	150.2	-	ns
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	
Q_r	Recovered charge		$T_{vj}=25^\circ C$	-	4.27	-	μC
			$T_{vj}=125^\circ C$	-	-	-	
			$T_{vj}=150^\circ C$	-	-	-	

E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	0.79	-	mJ
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
R _{thJC}	Thermal resistance, junction to case	per diode	-	-	0.58	-	K/W
R _{thCH}	Thermal resistance, case to heatsink	per diode, λ _{grease} =1 W/(m·K)	-	0.205	-	-	K/W
T _{vjop}	Temperature under switching conditions		-40			150	°C

Diode, Rectifier

Maximum Rated Values							
Symbol	Item	Conditions	Rating			Unit	
V _{RRM}	Repetitive peak reverse voltage	T _{vj} =25°C	1600			V	
I _{FRMSM}	Maximum RMS forward current per chip	T _C =80°C, T _{vj} =175°C	80			A	
I _{RMSM}	Maximum RMS current at rectifier output	T _C =80°C	115			A	
I _{FSM}	Surge forward current	t _p = 10 ms, T _{vj} =150°C	400			A	
I ² t	I ² t-value	V _R =0V, t _p =10ms, T _{vj} =150°C	800			A ² s	
Characteristic Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
V _F	Continuous forward voltage	I _F =75A V _{GE} =0V	T _{vj} =25°C	-	1.28	-	V
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
I _R	Reverse current	V _R =1600V	T _{vj} =25°C	-	-	10	uA
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
T _{vjop}	Temperature under switching conditions		-40			150	°C

IGBT , Brake-Chopper

Maximum Rated Values							
Symbol	Item	Conditions	Values			Unit	
V _{CES}	Collector-emitter voltage	T _{vj} =25°C	1200			V	
V _{GES}	Gate-emitter voltage	-	±20			V	
I _C	Collector current,DC	T _C =100°C, T _{vj} =175°C	50			A	
I _{CRM}	Repetitive peak collector current	t _p =1ms	100			A	
P _{tot}	Total power dissipation	T _C =25°C, T _{vj} =175°C	250			W	
Characteristic Values							
Symbol	Item	Conditions	Values			Unit	
			Min.	Typ.	Max.		
I _{CES}	Collector-emitter cut-off current	V _{CE} =1200V, V _{GE} =0V, T _{vj} =25°C	-	-	1	mA	
I _{GES}	Gate leakage current	V _{CE} =0V, V _{GE} =20V, T _{vj} =25°C	-	-	500	nA	
V _{GE(th)}	Gate-emitter threshold voltage	I _C =1.5mA, V _{CE} =V _{GE} , T _{vj} =25°C	5.2	5.5	6.2	V	

V_{CEsat}	Collector-emitter saturation voltage	$I_C=50A$ $V_{GE}=15V$	$T_{vj}=25^{\circ}C$	-	2.22	-	
			$T_{vj}=125^{\circ}C$	-	-	-	
			$T_{vj}=150^{\circ}C$	-	-	-	
C_{ies}	Input capacitance	$V_{CE}=25V, V_{GE}=0V$ $f=1MHz, T_{vj}=25^{\circ}C$	-	3.15	-	nF	
C_{oes}	Output capacitance		-	0.18	-		
C_{res}	Reverse transfer capacitance		-	0.103	-		
Q_G	Gate charge	$V_{CC}=600V, I_C=50A$ $V_{GE}=-15...+15V, T_{vj}=25^{\circ}C$	-	316	-	nC	
R_g	Internal gate resistance	$T_{vj}=25^{\circ}C$	-	-	-	Ω	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600V$ $I_C=50A$ $V_{GE}=\pm 15V$ $R_{G(on)}=10\Omega$ $R_{G(off)}=10\Omega$	$T_{vj}=25^{\circ}C$	-	53.4	-	ns
			$T_{vj}=125^{\circ}C$	-	-	-	
			$T_{vj}=150^{\circ}C$	-	-	-	
t_r	Rise time		$T_{vj}=25^{\circ}C$	-	36.7	-	
			$T_{vj}=125^{\circ}C$	-	-	-	
			$T_{vj}=150^{\circ}C$	-	-	-	
$t_{d(off)}$	Turn-off delay time		$T_{vj}=25^{\circ}C$	-	209.0	-	
			$T_{vj}=125^{\circ}C$	-	-	-	
			$T_{vj}=150^{\circ}C$	-	-	-	
t_f	Fall time	$T_{vj}=25^{\circ}C$	-	192.0	-		
		$T_{vj}=125^{\circ}C$	-	-	-		
		$T_{vj}=150^{\circ}C$	-	-	-		
E_{on}	Turn-on energy (per pulse)	$T_{vj}=25^{\circ}C$	-	3.43	-	mJ	
		$T_{vj}=125^{\circ}C$	-	-	-		
		$T_{vj}=150^{\circ}C$	-	-	-		
E_{off}	Turn-off energy (per pulse)	$T_{vj}=25^{\circ}C$	-	2.20	-		
		$T_{vj}=125^{\circ}C$	-	-	-		
		$T_{vj}=150^{\circ}C$	-	-	-		
SC data	Short-circuit current	$V_{CC}=600V, V_{GE}\leq 15V, T_{vj}=125^{\circ}C$ $V_{CES}\leq 1200V, t_p\leq 10\mu s$	-	178	-	A	
R_{thJC}	Thermal resistance, junction to case	Per IGBT	-	-	0.60	K/W	
R_{thCH}	Thermal resistance, case to heatsink	Per IGBT $\lambda_{grease}=1W/(m\cdot K)$	-	0.21	-	K/W	
T_{vjop}	Temperature under switching conditions		-40		150	$^{\circ}C$	

Diode , Brake-Chopper
Maximum Rated Values

Symbol	Item	Conditions	Rating	Unit
V_{RRM}	Repetitive peak reverse voltage	$T_{vj}=25^{\circ}C$	1200	V
I_F	Forward current, DC		25	A
I_{FRM}	Repetitive peak forward current	$t_p=1ms$	50	A
I^2t	I^2t -value	$V_R=0V, t_p=10ms, T_{vj}=125^{\circ}C$	170	A^2s

Characteristic Values

V_F	Continuous forward voltage	$I_F=25A$ $V_{GE}=0V$	$T_{vj}=25^{\circ}C$	-	2.21	-	V
			$T_{vj}=125^{\circ}C$	-	-	-	
			$T_{vj}=150^{\circ}C$	-	-	-	

I _{RM}	Peak reverse recovery current	V _R =600V I _F =50A V _{GE} =-15V R _{G(on)} =10Ω R _{G(off)} =10Ω	T _{vj} =25°C	-	54.5	-	A
			T _{vj} =125°C	-	-	-	
			T _{vj} =150°C	-	-	-	
t _{rr}	Reverse recovery time		T _{vj} =25°C	-	155.8	-	ns
			T _{vj} =125°C	-	-	-	
Q _r	Recovered charge		T _{vj} =25°C	-	2.87	-	μC
			T _{vj} =125°C	-	-	-	
E _{rec}	Reverse recovery energy		T _{vj} =25°C	-	0.68	-	mJ
			T _{vj} =125°C	-	-	-	
R _{thJC}	Thermal resistance, junction to case	per diode	-	-	1.20	-	K/W
R _{thCH}	Thermal resistance, case to heatsink	per diode, λ _{grease} =1 W/(m·K)	-	0.425	-	-	K/W
T _{vjop}	Temperature under switching conditions		-40		150		°C

Note:

IGBT electrical characteristics according to IEC 60747 – 9

Diode electrical characteristics according to IEC 60747 – 2

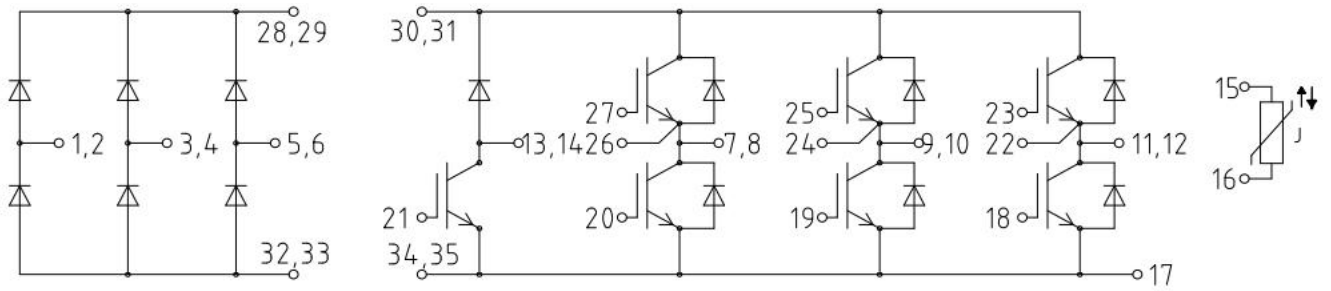
Module

Symbol	Item	Conditions	Rating			Unit
V _{ISOL}	Isolation voltage	Terminals to baseplate, RMS, f=50Hz, t=1min	2500			V
T _{vj max}	Maximum junction temperature	-	175			°C
T _{vj op}	Operating junction temperature	Continuous operation (underswitching)	-40~150			°C
T _{stg}	Storage temperature	-	-40~125			°C
Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
M	Mounting torque for module mounting	-	3	-	6	Nm
ds	Creepage distance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	10	-	
da	Clearance	Terminal to terminal	-	-	-	mm
		Terminal to base plate	-	7.5	-	
m	Weight	-	-	290	-	g

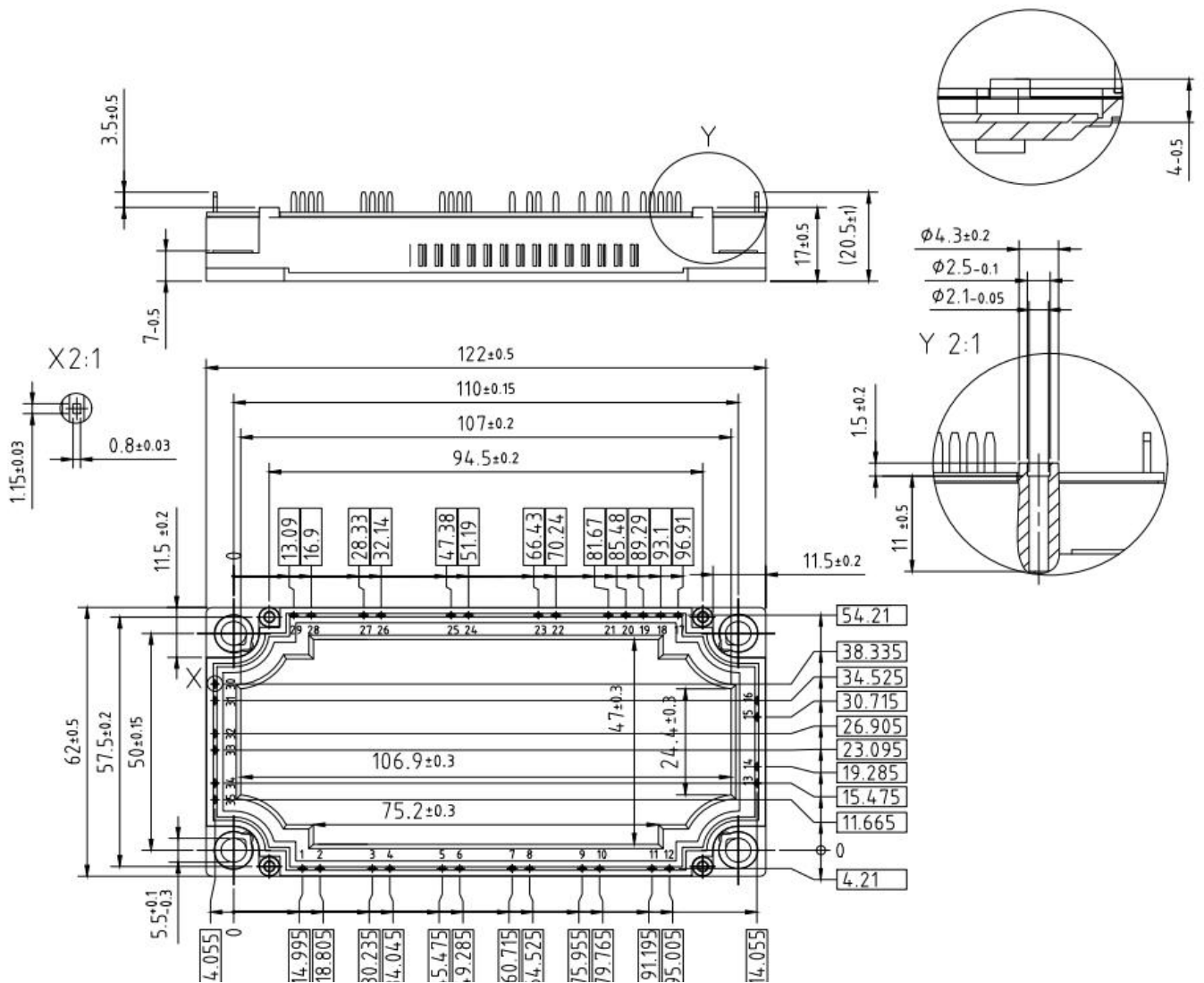
NTC Thermistor Characteristics

Symbol	Item	Conditions	Values			Unit
			Min.	Typ.	Max.	
R ₂₅	Rated resistance	T _C =25°C	-	5	-	kΩ
ΔR/R	Deviation of resistance	T _C =100°C, R ₁₀₀ =493Ω	-5	-	5	%
P ₂₅	Power dissipation	T _C =25°C	-	-	20	mW
B _{25/50}	B-constant	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]	-	3375	-	K
B _{25/80}	B-constant	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]	-	3411	-	
B _{25/100}	B-constant	R ₂ =R ₂₅ exp[B _{25/100} (1/T ₂ -1/(298.15K))]	-	3433	-	

Circuit Diagram



Package Outlines



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